

What is claimed is:

1. A semiconductor light emitting device, comprising:

a semiconductor substrate;

5 a light emitting layer forming portion provided on said semiconductor substrate, in which an active layer made of a compound semiconductor is sandwiched between a first clad layer and a second clad layer made of compound semiconductor having band gap greater than that of said active layer, respectively and having a different 10 conductivity type each other; and

a window layer provided at least above said second clad layer,

wherein said second clad layer is made of a compound semiconductor having a refractive index greater 15 than that of said first clad layer provided on said semiconductor substrate side.

2. The semiconductor light emitting device according to claim 1, wherein said window layer is made of a compound semiconductor having a refractive index 20 greater than that of said second clad layer.

3. The semiconductor light emitting device according to claim 1, wherein the refractive index of said second clad layer is greater than the refractive index of said first clad layer by 6% to 4%.

25 4. The semiconductor light emitting device according to claim 1, wherein said first clad layer is

made of  $In_{0.49}(Ga_{1-s}Al_s)_{0.51}P$  ( $0.6 \leq s \leq 1$ ) and said second clad layer is made of  $In_{0.49}(Ga_{1-y}Al_y)_{0.51}P$  ( $0.4 \leq y \leq 0.75$ ,  $y < s$ ).

5. The semiconductor light emitting device according to claim 4, wherein said window layer is made of  $Al_vGa_{1-v}As$  ( $0.6 \leq v \leq 0.85$ ).

6. The semiconductor light emitting device according to claim 1, wherein said first clad layer is made of  $Al_zGa_{1-z}As$  ( $0.6 \leq z \leq 0.9$ ) and said second clad 10 layer is made of  $Al_uGa_{1-u}As$  ( $0.4 < u \leq 0.85$ ,  $u < z$ ).

7. The semiconductor light emitting device according to claim 6, wherein said window layer is made of  $Al_wGa_{1-w}As$  ( $0.4 \leq w < 0.7$ ,  $w < u$ ).

8. The semiconductor light emitting device 15 according to claim 1, wherein a substrate side window layer is formed on said semiconductor substrate side of said first clad layer and said substrate side window layer is made of a material having a refractive index smaller than that of said first clad layer.